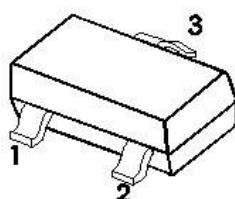


SOT-23**SOT-23 Plastic-Encapsulate Schottky Barrier Diode****特征 Features**

- 大电流承受能力。High Current Capability
- 正向压降低。Low Forward Voltage Drop
- 开关速度快。Extremely Fast Switching Speed

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

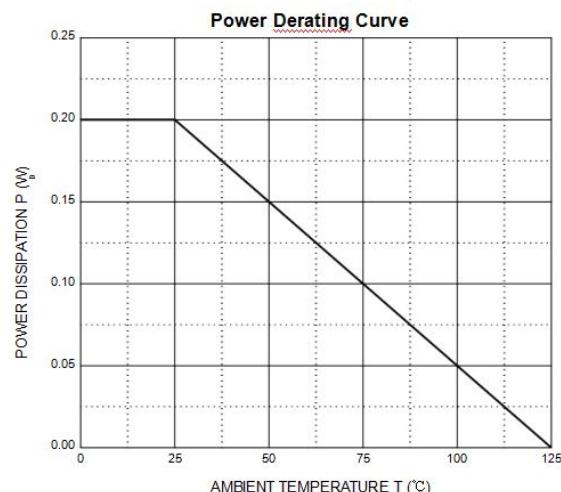
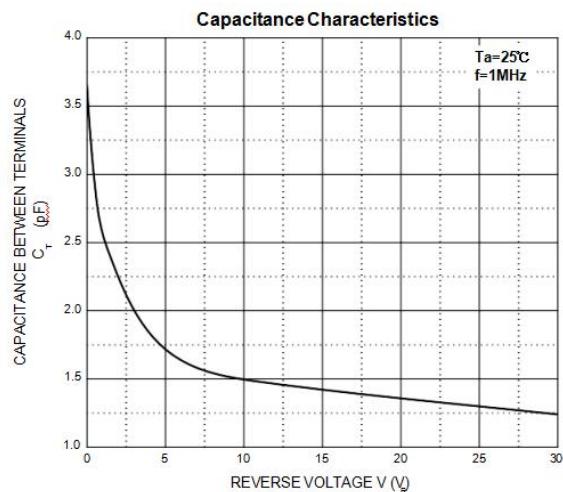
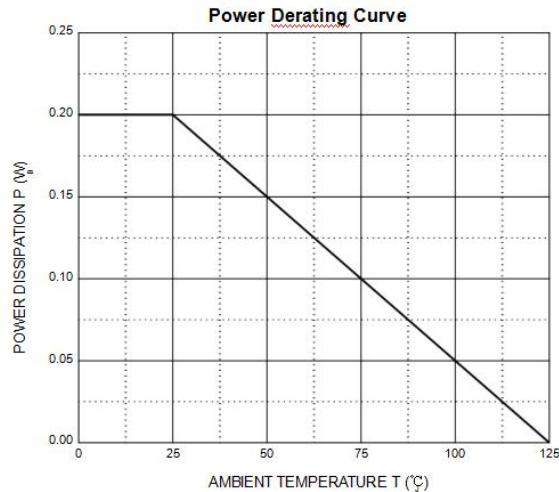
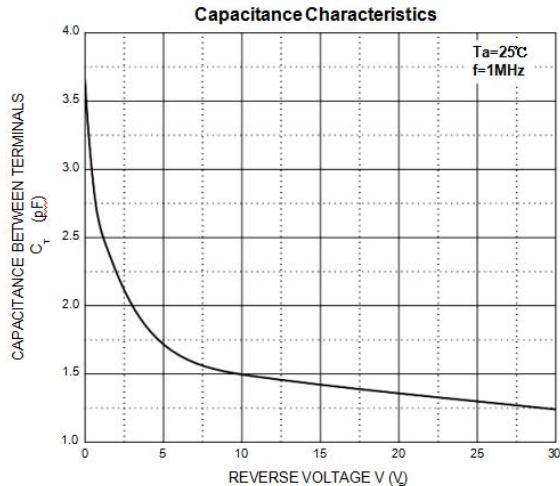
Marking: 43 •**极限值和温度特性(TA = 25°C 除非另有规定)****Maximum Ratings & Thermal Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	VR	40	V
反向峰值电压 Peak Repetitive Reverse Voltage	VRMM	40	V
功率消耗 Power Dissipation	Pd	200	mW
典型热阻 Typical thermal resistance	RθJA	500	°C/W
结温 Junction Temperature	Tj	125	°C
存储温度 Storage temperature range	TSTG	-55~+150	°C
最大正向平均整流电流 Maximum average forward rectified current	IFM	200	mA
峰值正向浪涌电流 8.3ms 单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	IFSM	600	mA

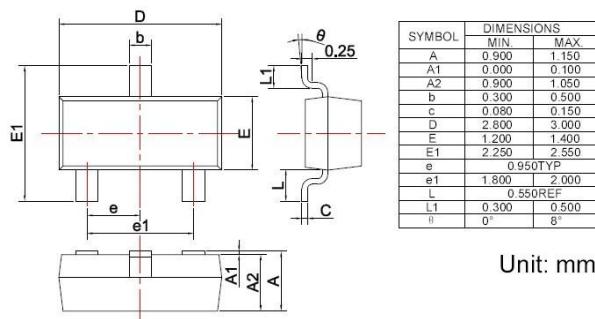
电特性 (TA = 25°C 除非另有规定)**Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
V(BR)	反向电压 Reverse Voltage	IR=10uA	40		V
IR	反向漏电电流 Reverse Leakage Current	VR=30V	---	200	nA
VF	正向电压 Forward Voltage	IF=1.0mA	---	0.38	V
		IF=40mA	---	1.0	
TRR	反向恢复时间 Reverse Recovery Time	IF= IR=10mA	---	5	nS
		RL=100Ω			
		IRR=0.1 X IR			
CT	结电容 Capacitance	VR=0V, f=1MHZ	--	5	pF

Typical Characteristics



SOT-23 PACKAGE OUTLINE Plastic surface mounted package

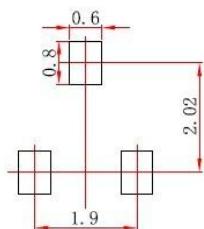


Unit: mm

焊盘设计参考

Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note:
 1. Controlling dimension: In millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.